

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IPA60R280C6

FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

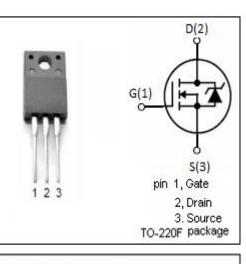
| • ABSOLUTE MAXIMUM RATINGS(Ta=25 C) | | | | | | | |
|-------------------------------------|---|-------------|------|--|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | | |
| V _{DSS} | Drain-Source Voltage | 600 | V | | | | |
| V _{GSS} | Gate-Source Voltage | ±20 | V | | | | |
| ID | Drain Current-Continuous @Tc=25℃ Tc=100℃ | 13.8 8.7 | A | | | | |
| I _{DM} | Drain Current-Single Pulsed | 40 | А | | | | |
| PD | Total Dissipation @Tc=25°C | 32 | W | | | | |
| T _{ch} | Max. Operating Junction Temperature | 150 | °C | | | | |
| T _{stg} | Storage Temperature | -55~150 | Ĉ | | | | |

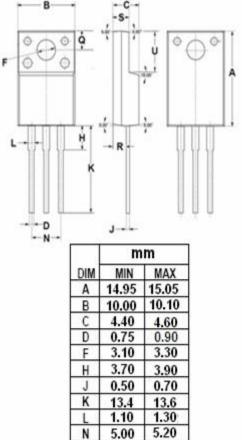
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|---|-----|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 3.9 | °C /W | |
| Rth(ch-a) | Rth(ch-a) Channel-to-ambient thermal resistance | | °C/W | |

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2.90

2.40

6.60

2.70

2.20

2.65

6.40

QR

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ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | МАХ | UNIT |
|----------------------|--------------------------------|--|-----|-----|---------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =0.25mA | 600 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = ±20V; I _D =0.43mA | 2.5 | | 3.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =6.5A | | 250 | 280 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} =0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V;Tj=25℃ V _{DS} = 600V; V _{GS} = 0V; Tj=150℃ | | | 1 10 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =6.5A, V _{GS} = 0 V | | 0.9 | | V |

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